

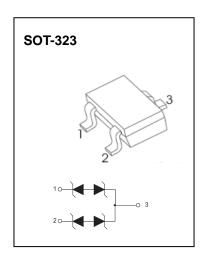
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Diodes

CESDB5V0AT3 ESD Protection Diode

DESCRIPTION

The CESDB5V0AT3 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.



FEATURES

- Reverse working (stand-off) Voltage: 5.0 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) Per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- This is a Pb-Free Device

Maximum Ratings @Ta=25℃

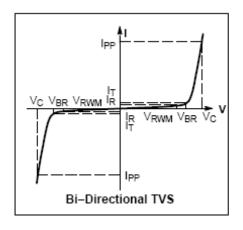
Param	Symbol	Limit	Unit	
IEC61000-4-2(ESD)	Air		±30	KV
	Contact		±30	KV
ESD Voltage	Per Human Body Model		16	KV
	Per Machine Model		400	V
Total Power Dissipation on FR-5 Board (Note 1)		\mathbf{P}_{D}	150	mW
Thermal Resistance Junction-to-A	$R_{\Theta JA}$	833	°C/W	
Lead Solder Temperature - Maximu	TL	260	°C	
Junction and Storage Temperature	T _{j,} T _{stg}	-55 ~ +150	℃	

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended. Operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.62$ in.

ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise noted)

Symbol	Parameter					
I _{PP}	Maximum Reverse Peak Pulse Current					
Vc	Clamping Voltage @ I _{PP}					
V_{RWM}	Working Peak Reverse Voltage					
I _R	Maximum Reverse Leakage Current @ V _{RWM}					
V_{BR}	Breakdown Voltage @ I _T					
I _T	Test Current					
С	Max. Capacitance @V _R =0 and f =1MHz					



ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted)

Device⁺	Device	V _{RWM} (V)	I _R (μΑ) @ V _{RWM}	V _{BR} (V) @ I _T (Note 2)		Ι _τ	Vc @IPP = 5 A	I _{PP} (A)	V _с (V) @Мах І _{РР}	C (pF)@ V _R =0V,f=1MHz
	Marking	Max	Max	Min	Max	mA	٧	Max	Max	Тур
CESDB5V0AT3	B5A	5.0	1.0	5.8	8.8	1.0	9	12.5	15	26.5

^{*}Other voltages available upon request.

^{2.} V_{BR} is measured with a pulse test current I_{T} at an ambient temperature of 25°C.